

Sub H' > 120. (Twice amended) The imaging device according to claim 1, further comprising a gate stack over said substrate, wherein said gate stack is disposed over an insulating layer of silicon dioxide which is over said substrate.

Sub I' > 121. (Twice amended) The imaging device according to claim 14, further comprising a gate stack over said substrate, wherein said gate stack is disposed over an insulating layer of silicon dioxide which is over said substrate.

E1 Sub F' 122. (Twice amended) The imaging device according to claim 28, further comprising a gate stack over said substrate, wherein said gate stack is disposed over an insulating layer of silicon dioxide which is over said substrate.

123. (Twice amended) The imaging device according to claim 39, further comprising a gate stack over said substrate, wherein said gate stack is disposed over an insulating layer of silicon dioxide which is over said substrate.

Sub I' > 124. (Twice amended) The imaging device according to claim 53, further comprising a gate stack over said substrate, wherein said gate stack is disposed over an insulating layer of silicon dioxide which is over said substrate.

E2 Sub H' > 135. (Amended) The imaging device according to claim 120, wherein said gate stack comprises a transfer gate stack and a reset gate stack.